

Supplementary Information

Indigo-based Highly Coplanar Semiconducting Polymer for N-Type Organic Thin Film Transistors

Chang Guo,^a Jesse Quinn,^a Bin Sun,^a and Yuning Li^{a*}

^a Department of Chemical Engineering/Waterloo Institute for Nanotechnology (WIN), University of Waterloo, 200 University Avenue West, Waterloo, Ontario, Canada N2L 3G1; Fax: +1 519-888-4347; Tel: +1 519-888-4567 ext. 31105; Email: yuning.li@uwaterloo.ca.

Contents

1. Computer simulations

Table S1 Summary of computer simulation results of model compounds, *trans*-IDBr and *trans*-IDBrAc.

2. Additional data

Fig. S1 The 300 MHz ¹H NMR spectrum of di-*tert*-butyl 6,6'-dibromo-3,3'-dioxo-[2,2'-biindolinylidene]-1,1'-dicarboxylate (compound **2**) measured in CDCl₃.

Fig. S2 The 75 MHz ¹³C NMR spectrum of di-*tert*-butyl 6,6'-dibromo-3,3'-dioxo-[2,2'-biindolinylidene]-1,1'-dicarboxylate (compound **2**) measured in CDCl₃.

Fig. S3 The 300 MHz ¹H NMR spectrum of 4,8-bis((2-decyltetradecyl)oxy)benzo[1,2-*b*:4,5-*b'*]dithiophene (compound **3**) measured in CDCl₃.

Fig. S4 The 300 MHz ¹H NMR spectrum of (4,8-bis((2-decyltetradecyl)oxy)benzo[1,2-*b*:4,5-*b'*]dithiophene-2,6-diyl)bis(trimethylstannane) (compound **4**) measured in CDCl₃.

Fig. S5 The 300 MHz ¹H NMR spectrum of **PIDBDT** measured in CDCl₃.

Fig. S6 DSC curves of **PIDBDT** with a heating rate of 10 °C min⁻¹ under N₂.

Fig. S7 Transfer and output curves of OTFT devices with **PIDBDT** thin films annealed at 250 °C for 1 h.

Fig. S8 UV-vis absorption spectra of **PIDBDT** films on glass substrates annealed at 200 °C for different periods of time.

Table S2 Performance of OTFT devices using **PIDBDT** annealed at 200 or 250 °C.

3. References

Supplementary Information

1. Computer simulations

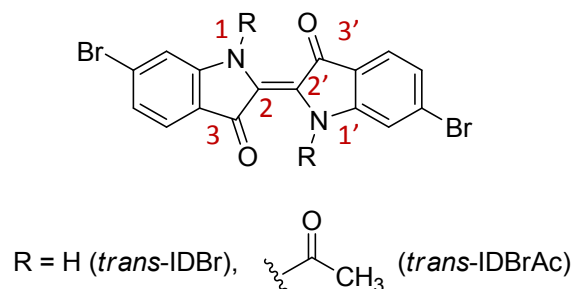
Geometry optimization of model compounds was performed based on the density functional theory (DFT) using the B3LYP hybrid function¹ and the 6-31G* basis set and the Gaussian 09W package² on the Shared Hierarchical Academic Research Computer Network (SHARCNET) of Canada.

The route used for all calculations was the following:

```
# opt=tight freq b3lyp/6-31g(d) guess=save geom=connectivity int=ultrafine
```

The obtained key dihedral angles of two model compounds, (*E*)-6,6'-dibromo-[2,2'-biindolinylidene]-3,3'-dione (or Tyrian Purple) (*trans*-IDBr) and (*E*)-1,1'-diacetyl-6,6'-dibromo-[2,2'-biindolinylidene]-3,3'-dione (*trans*-IDBrAc) are summarized in Table S1.

Table S1. Summary of computer simulation results of model compounds, *trans*-IDBr and *trans*-IDBrAc.



Model compound	Dihedral angle, °		
	N(1)-C(2)-C(2')-N(1')	N(1)-C(2)-C(2')-C(3')	C(3)-C(2)-C(2')-C(3')
<i>trans</i> -IDBr	180	0	180
<i>trans</i> -IDBrAc	173.3	22.6/24.5	139.5

Supplementary Information

2. Additional data

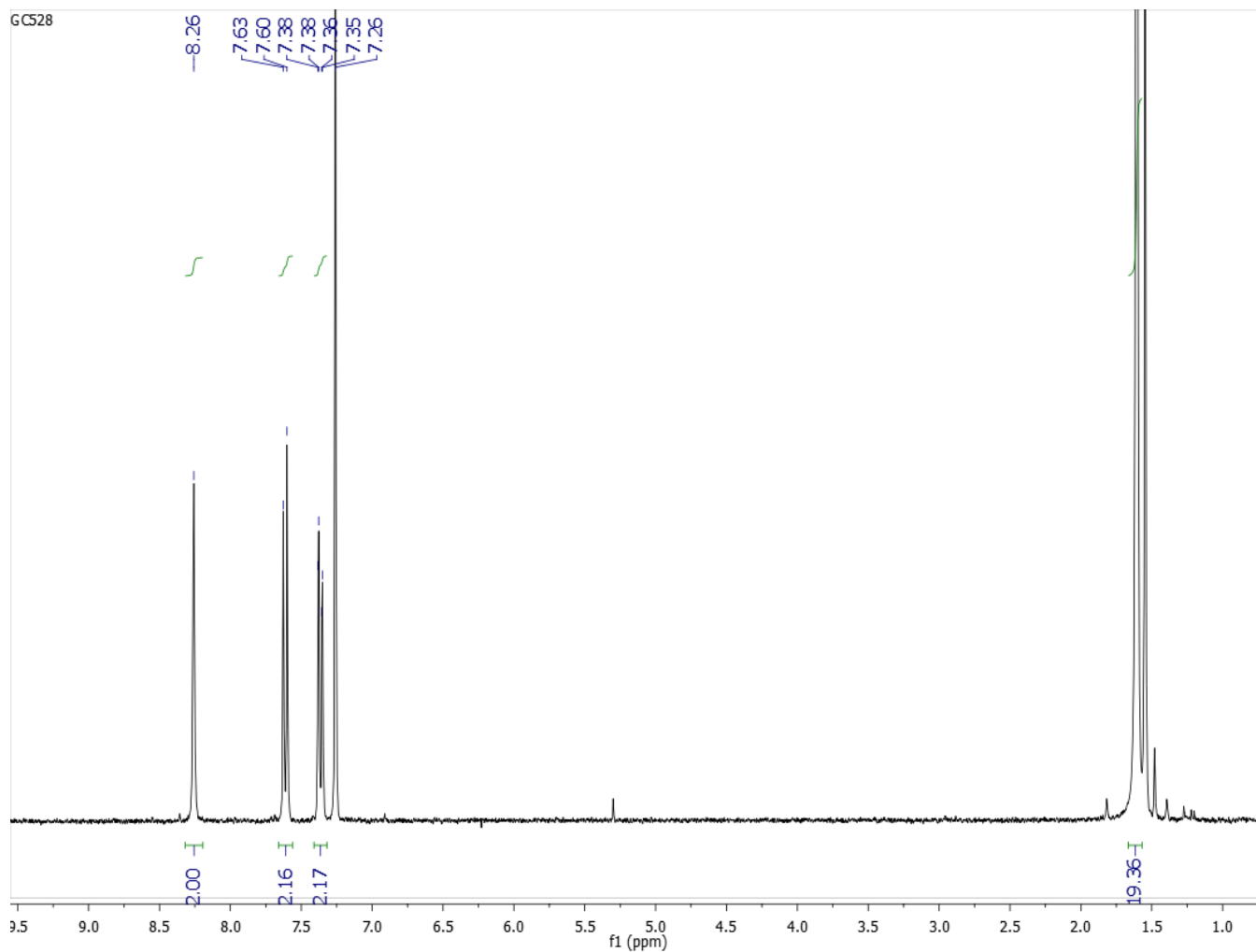


Fig. S1 The 300 MHz ^1H NMR spectrum of di-*tert*-butyl 6,6'-dibromo-3,3'-dioxo-[2,2'-biindolylidene]-1,1'-dicarboxylate (compound **2**) measured in CDCl_3 .

Supplementary Information

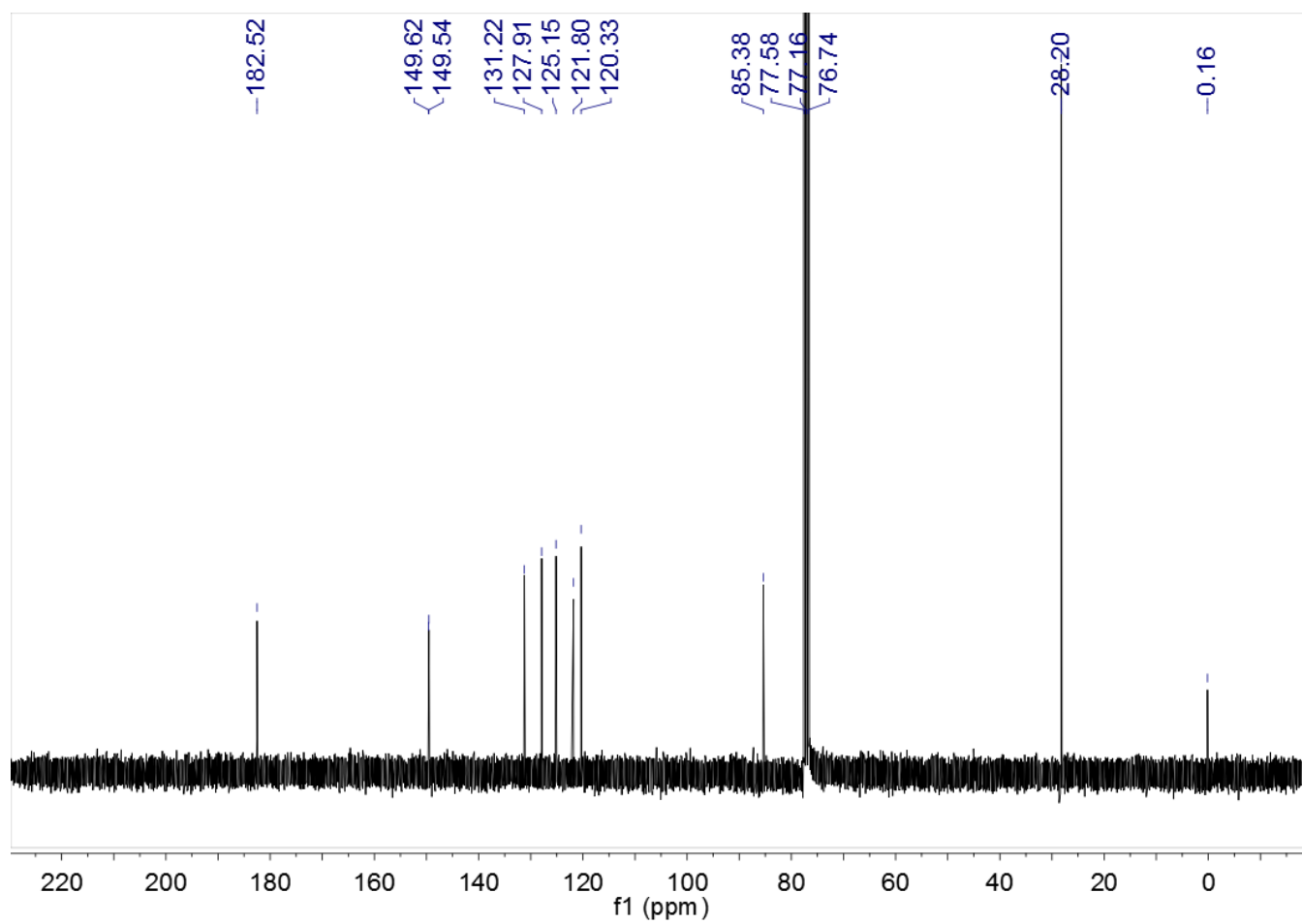


Fig. S2 The 75 MHz ^{13}C NMR spectrum of di-*tert*-butyl 6,6'-dibromo-3,3'-dioxo-[2,2'-biindolinylidene]-1,1'-dicarboxylate (compound **2**) measured in CDCl_3 .

Supplementary Information

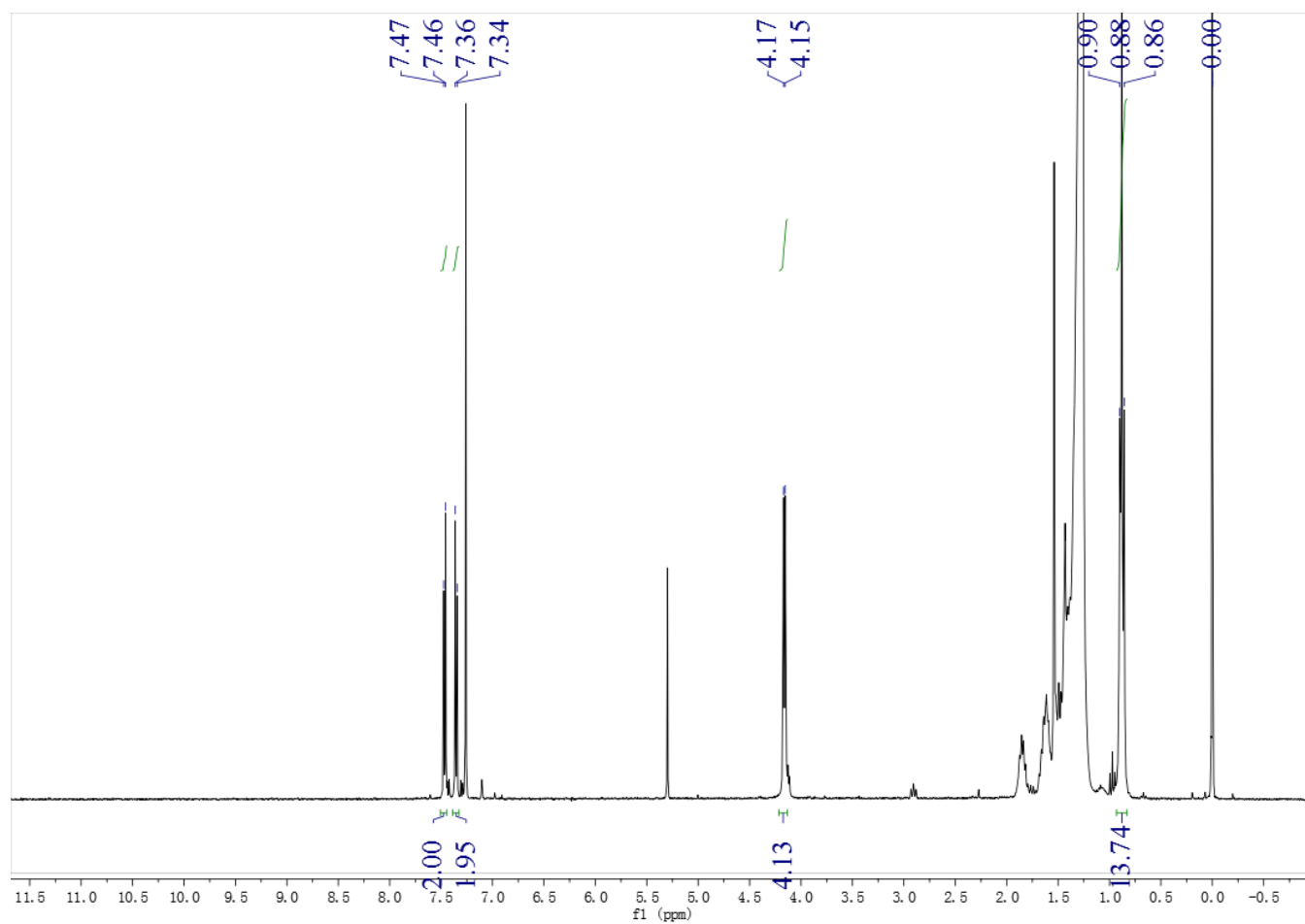


Fig. S3 The 300 MHz ¹H NMR spectrum of 4,8-bis((2-decyltetradecyl)oxy)benzo[1,2-*b*:4,5-*b'*]dithiophene (compound **3**) measured in CDCl₃.

Supplementary Information

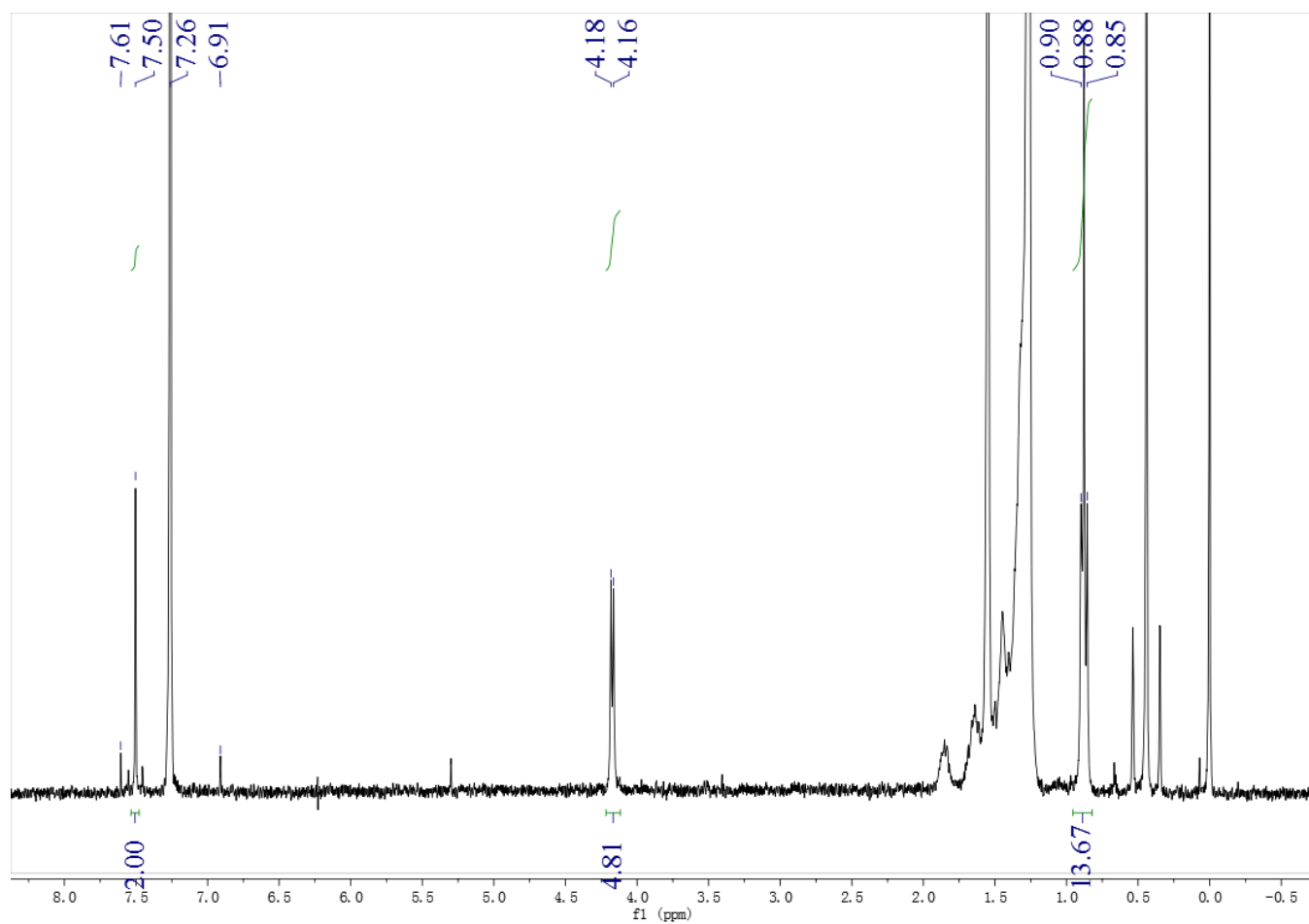


Fig. S4 The 300 MHz ¹H NMR spectrum of (4,8-bis((2-decyltetradecyl)oxy)benzo[1,2-*b*:4,5-*b'*]dithiophene-2,6-diyl)bis(trimethylstannane) (compound **4**) measured in CDCl₃.

Supplementary Information

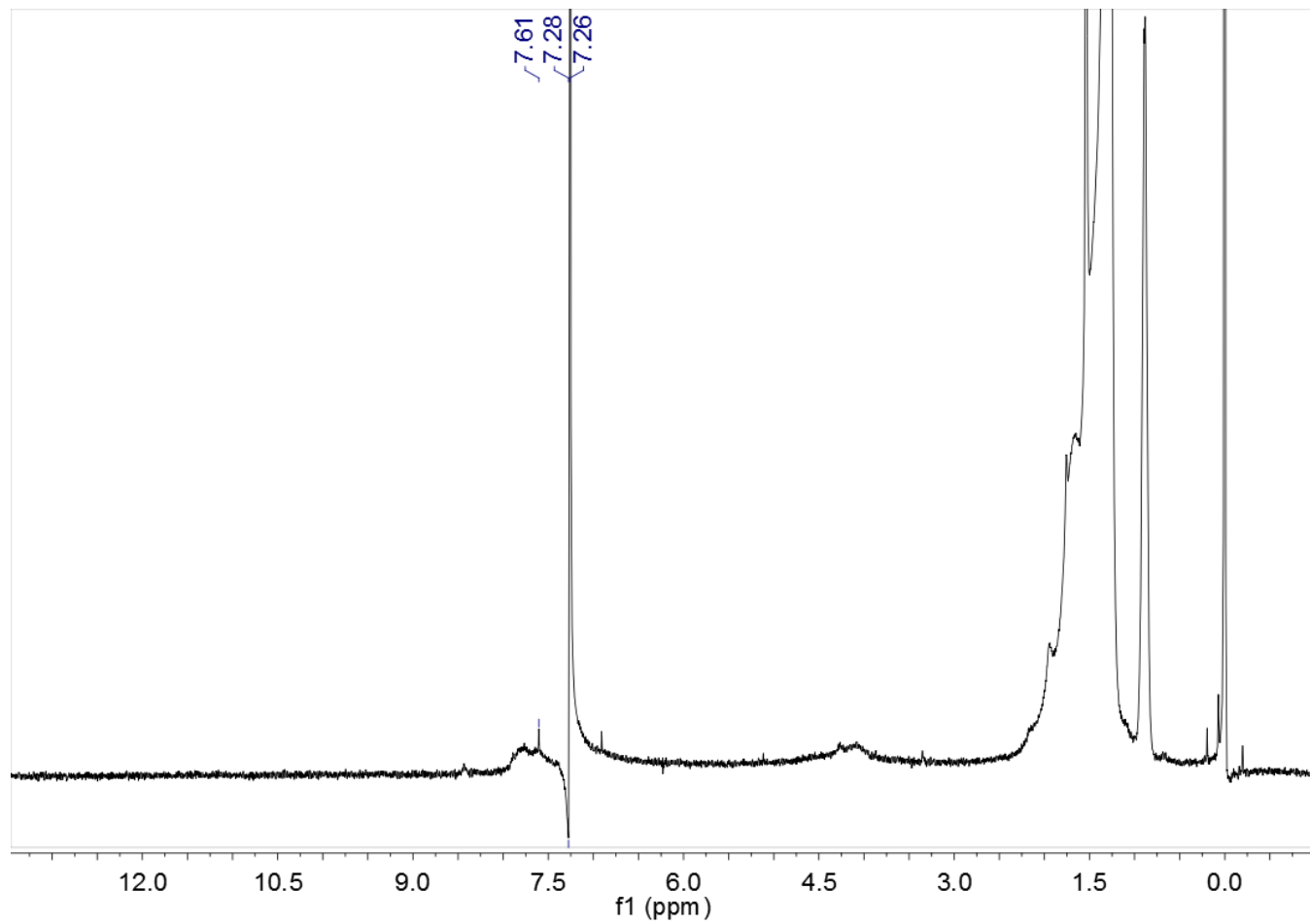


Fig. S5 The 300 MHz ^1H NMR spectrum of **PIDBDT** measured in CDCl_3 .

Supplementary Information

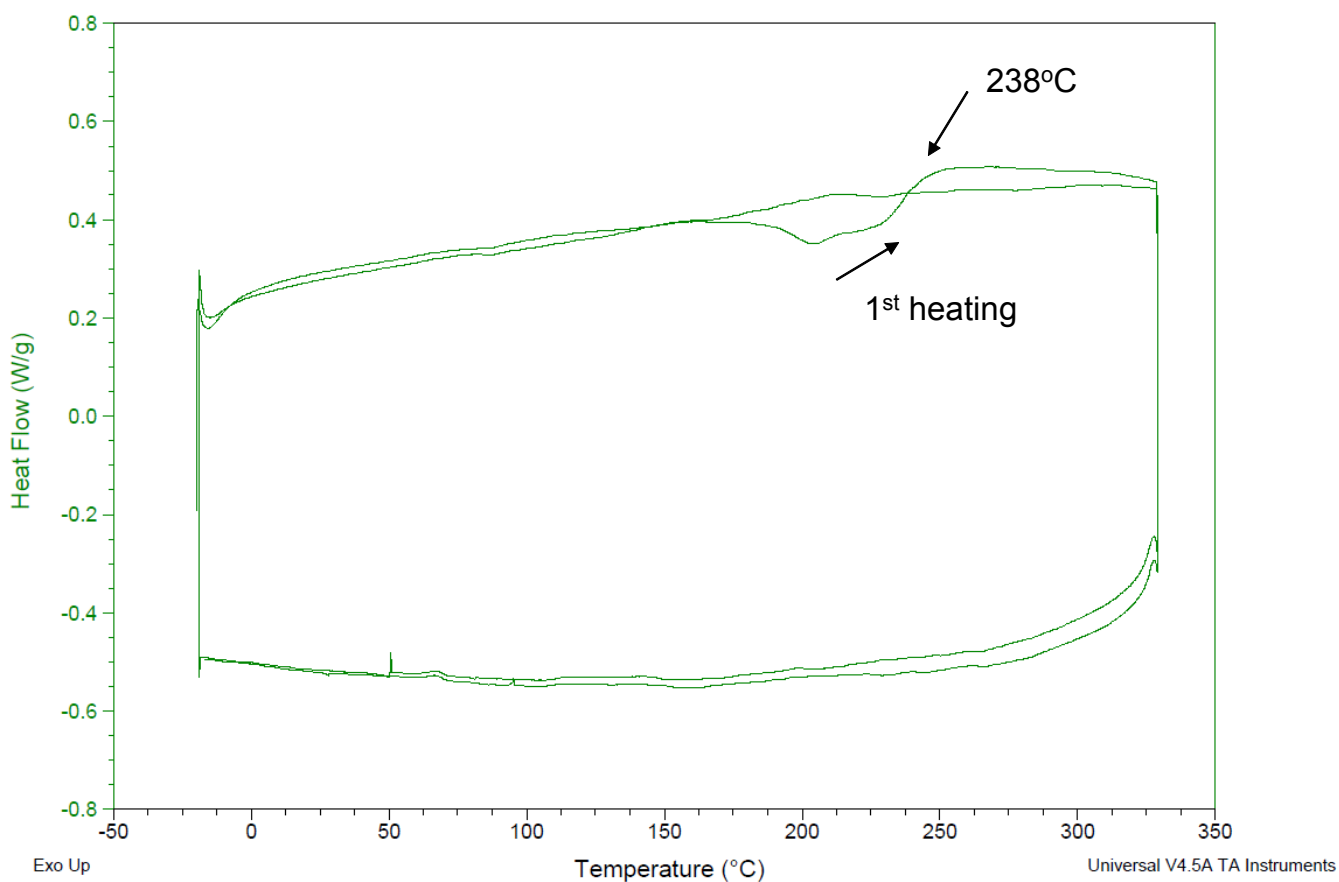


Fig. S6 DSC curves of **PIDBDT** with a heating rate of $10\text{ }^{\circ}\text{C}\cdot\text{min}^{-1}$ under N_2 .

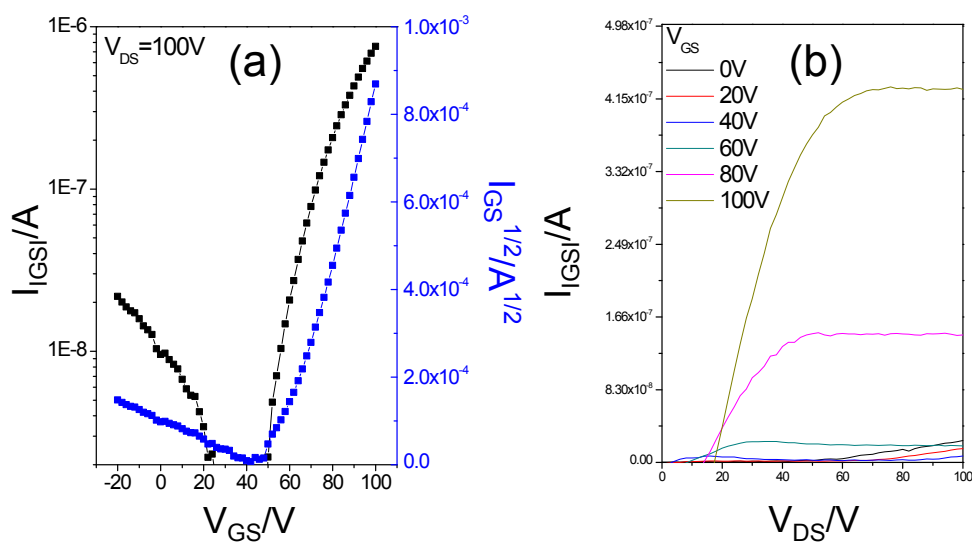


Fig. S7 Transfer and output curves of OTFT devices with **PIDBDT** thin films annealed at $250\text{ }^{\circ}\text{C}$ for 1 h.

Device dimensions: channel width (W) = 1 mm; channel length (L) = $30\text{ }\mu\text{m}$.

Supplementary Information

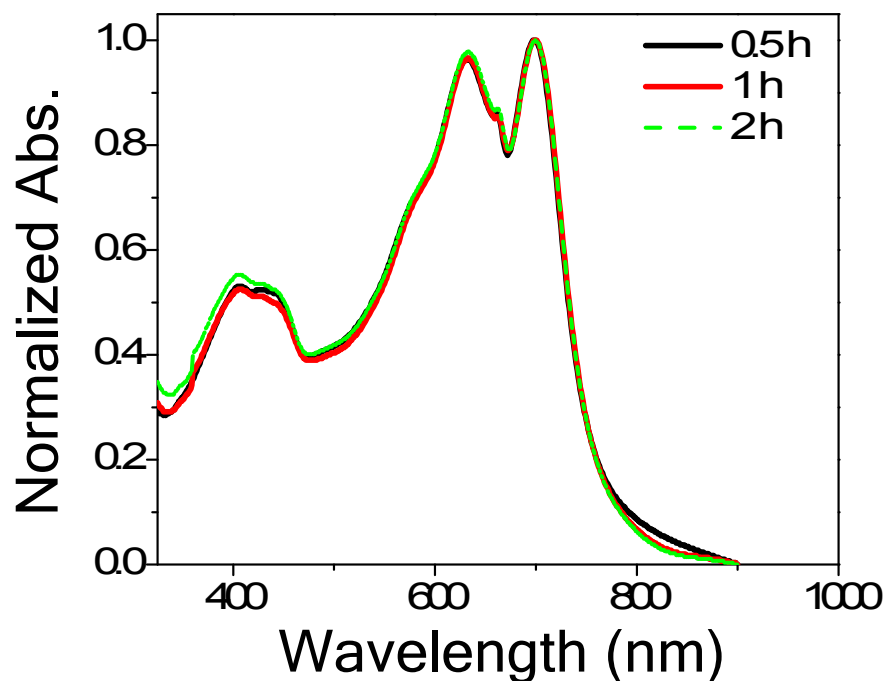


Fig. S8 UV-vis absorption spectra of **PIDBDT** films on glass substrates annealed at 200 °C for different periods of time.

Table S2. Performance of OTFT devices using PIDBDT annealed at 200 or 250 °C.^a

Annealing temperature / time	Average electron mobility, μ_e ($\text{cm}^2\text{V}^{-1}\text{s}^{-1}$)	Maximum electron mobility, μ_e ($\text{cm}^2\text{V}^{-1}\text{s}^{-1}$)	Standard deviation ($\text{cm}^2\text{V}^{-1}\text{s}^{-1}$)	Threshold voltage, V_{th} (V)	Current on-to-off ratio, I_{on}/I_{off}	Drain voltage, V_{DS} (V)
200 °C / 0.5 h	3.1×10^{-3}	3.9×10^{-3}	4.5×10^{-4}	39.7-55.3	$\sim 10^3$	100
200 °C / 1 h	4.9×10^{-3}	5.7×10^{-3}	4.7×10^{-4}	32.2-57.5	$\sim 10^3$	100
200 °C / 3 h	4.1×10^{-3}	4.9×10^{-3}	4.2×10^{-4}	35.7-56.7	$\sim 10^3$	100
250 °C / 1 h	2.5×10^{-3}	3.1×10^{-3}	4.4×10^{-4}	42.2-57.6	$\sim 10^3$	100

^a Data were collected from at least five devices for each condition.

Supplementary Information

3. References

1. (a) A. D. Becke, *Phys. Rev. A*, 1988, 38, 3098. (b) C. Lee, W. Yang and G. G. Parr, *Phys. Rev. B*, 1988, 37, 785.
2. (a) \AA . Frisch, *Gaussian 09W Reference*, Gaussian, Inc., Wallingford, CT, 2009. (b) *Gaussian 09, Revision B.01*, M. J. Frisch, G. W. Trucks, H. B. Schlegel, G. E. Scuseria, M. A. Robb, J. R. Cheeseman, G. Scalmani, V. Barone, B. Mennucci, G. A. Petersson, H. Nakatsuji, M. Caricato, X. Li, H. P. Hratchian, A. F. Izmaylov, J. Bloino, G. Zheng, J. L. Sonnenberg, M. Hada, M. Ehara, K. Toyota, R. Fukuda, J. Hasegawa, M. Ishida, T. Nakajima, Y. Honda, O. Kitao, H. Nakai, T. Vreven, J. A. Montgomery, Jr., J. E. Peralta, F. Ogliaro, M. Bearpark, J. J. Heyd, E. Brothers, K. N. Kudin, V. N. Staroverov, R. Kobayashi, J. Normand, K. Raghavachari, A. Rendell, J. C. Burant, S. S. Iyengar, J. Tomasi, M. Cossi, N. Rega, J. M. Millam, M. Klene, J. E. Knox, J. B. Cross, V. Bakken, C. Adamo, J. Jaramillo, R. Gomperts, R. E. Stratmann, O. Yazyev, A. J. Austin, R. Cammi, C. Pomelli, J. W. Ochterski, R. L. Martin, K. Morokuma, V. G. Zakrzewski, G. A. Voth, P. Salvador, J. J. Dannenberg, S. Dapprich, A. D. Daniels, Ö. Farkas, J. B. Foresman, J. V. Ortiz, J. Cioslowski and D. J. Fox, *Gaussian, Inc.*, Wallingford CT, 2009.